

IN THE SPECIFICATION

The Applicant hereby amends the paragraph starting on page 3, line 11 of the “clean copy” of the specification most recently provided, as follows:

The annular structures arranged on the thick oxide layer and defined by a surface material different from the remaining surface material may have different surface conductivities and thus may form different, for example higher, contact resistances. The overall effect may be to increase the surface resistance between the guard ring and the FET so that the concentration rise per unit time of a gas signal may be increased.